

Small-Signal Switching Diode

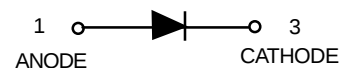
- Silicon Epitaxial Planar Diode
- Fast switching Diode;
especially suited for applications requiring high
voltage capability

LSD2004LT1

SOT- 23

DEVICE MARKING

LSD2004LT1=DB5



MAXIMUM RATINGS AND THERMAL CHARACTERISTICS

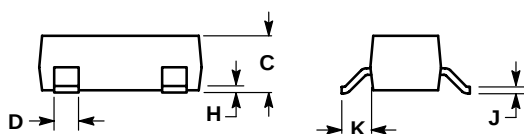
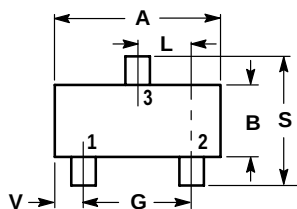
Characteristic	Symbol	MIN	Max	Unit
Continuous Reverse Voltage	V_R	240		V
Reverse Breakdown Voltage ($I_R = 100\mu A$)	$V_{(BR)}$	300		V
Reverse Voltage Leakage Current ($V_R = 240V$)	I_R		100	nA
($V_R = 240V, T_j = 150^\circ C$)	I_R		100	μA
Forward Voltage ($I_F = 20 mA$)	V_F		870	mV
($I_F = 100 mA$)	V_F		1000	mV
Reverse Recovery Time ($I_F = 30 mA, I_{rr} = 3.0 mA$)	T_{rr}		50	ns
Capacitance ($V_F = V_R = 0, F = 1MHz$)	C		5.0	pF
Forward Current (continuous)	I_F		225	mA

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NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M,1982
2. CONTROLLING DIMENSION: INCH.



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

PIN 1. BASE
2. EMITTER
3. COLLECTOR

